

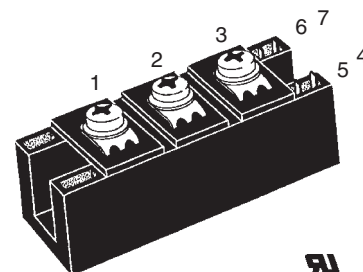
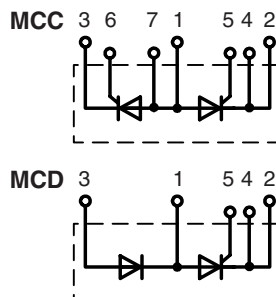
High Voltage Thyristor Module

$$I_{TRMS} = 2 \times 300 \text{ A}$$

$$I_{TAVM} = 2 \times 165 \text{ A}$$

$$V_{RRM} = 2000-2200 \text{ V}$$

V_{RSM}	V_{RRM}	Type	
V_{DSM}	V_{DRM}		
V	V		
2100	2000	MCC 161-20io1	MCD 161-20io1
2300	2200	MCC 161-22io1	MCD 161-22io1



Symbol	Conditions	Maximum Ratings	
I_{TRMS}	$T_{VJ} = T_{VJM}$	300	A
I_{TAVM}	$T_C = 85^\circ\text{C}; 180^\circ \text{ sine}$	165	A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}; t = 10 \text{ ms (50 Hz)}$	6000	A
	$V_R = 0; t = 8.3 \text{ ms (60 Hz)}$	6400	A
	$T_{VJ} = T_{VJM}; t = 10 \text{ ms (50 Hz)}$	5250	A
	$V_R = 0; t = 8.3 \text{ ms (60 Hz)}$	5600	A
I^2dt	$T_{VJ} = 45^\circ\text{C}; t = 10 \text{ ms (50 Hz)}$	180000	A ² s
	$V_R = 0; t = 8.3 \text{ ms (60 Hz)}$	170000	A ² s
	$T_{VJ} = T_{VJM}; t = 10 \text{ ms (50 Hz)}$	137000	A ² s
	$V_R = 0; t = 8.3 \text{ ms (60 Hz)}$	128000	A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM};$ repetitive, $I_T = 500 \text{ A}$ $f = 50 \text{ Hz}; t_p = 200 \mu\text{s};$ $V_D = \frac{2}{3} V_{DRM};$	150	A/ μs
	$I_G = 0.5 \text{ A};$ non repetitive, $I_T = I_{TAVM}$ $di_G/dt = 0.5 \text{ A}/\mu\text{s}$	500	A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}; V_{DR} = \frac{2}{3} V_{DRM0}$ $R_{GK} = \infty;$ method 1 (linear voltage rise)	1000	V/ μs
P_{GM}	$T_{VJ} = T_{VJM}; t_p = 30 \mu\text{s}$	120	W
	$I_T = I_{TAVM}; t_p = 500 \mu\text{s}$	60	W
P_{GAV}		8	W
V_{RGM}		10	V
T_{VJ}		-40...125	$^\circ\text{C}$
T_{VJM}		125	$^\circ\text{C}$
T_{stg}		-40...125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS; $t = 1 \text{ min}$	3000	V~
	$I_{ISOL} \leq 1 \text{ mA}; t = 1 \text{ s}$	3600	V~
M_d	Mounting torque (M6)	2.25-2.75	Nm
	Terminal connection torque (M6)	4.5-5.5	Nm
Weight	Typical including screws	125	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated

Features

- International standard package
- Direct Copper Bonded Al_2O_3 -ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 72873
- Keyed gate/cathode twin pins

Applications

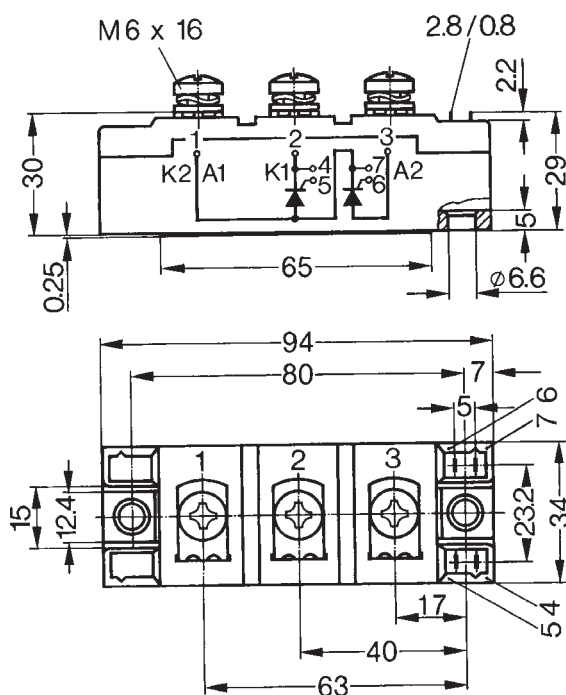
- Motor control
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Contactless switches

Advantages

- Space and weight savings
- Simple mounting
- Improved temperature and power cycling
- Reduced protection circuits

Symbol	Conditions	Characteristic Values	
I_{RRM}, I_{DRM}	$V_R = V_{RRM}; T_{VJ} = T_{VJM}$	40	mA
V_T	$I_T = 300A; T_{VJ} = 25^\circ C$	1.36	V
V_{T0}	For power-loss calculations only ($T_{VJ} = T_{VJM}$)	0.8	V
r_T		1.6	mΩ
V_{GT}	$V_D = 6 V; T_{VJ} = 25^\circ C$	2	V
	$T_{VJ} = -40^\circ C$	2.6	V
I_{GT}	$V_D = 6 V; T_{VJ} = 25^\circ C$	150	mA
	$T_{VJ} = -40^\circ C$	200	mA
V_{GD}	$V_D = \frac{2}{3} V_{DRM}; T_{VJ} = T_{VJM}$	0.25	V
I_{GD}	$V_D = \frac{2}{3} V_{DRM}; T_{VJ} = T_{VJM}$	10	mA
I_L	$T_{VJ} = 25^\circ C; V_D = 6 V; t_p = 30 \mu s$ $di_G/dt = 0.45 A/\mu s; I_G = 0.45 A$	200	mA
I_H	$T_{VJ} = 25^\circ C; V_D = 6 V; R_{GK} = \infty$	150	mA
t_{gd}	$T_{VJ} = 25^\circ C; V_D = 1/2 V_{DRM}$ $di_G/dt = 0.5 A/\mu s; I_G = 0.5 A$	2	μs
t_q	$T_{VJ} = T_{VJM}; V_R = 100 V; V_D = \frac{2}{3} V_{DRM}; t_p = 200 \mu s$ $dv/dt = 20 V/\mu s; I_T = 160 A; -di/dt = 10A/\mu s$	typ. 150	μs
Q_S	$T_{VJ} = T_{VJM}$ $-di/dt = 50 A/\mu s; I_T = 300 A$	550	μC
I_{RM}		235	A
R_{thJC}	per thyristor; DC current	0.155	K/W
	per module	0.078	K/W
R_{thJK}	per thyristor; DC current	0.225	K/W
	per module	0.113	K/W
d_s	Creeping distance on surface	12.7	mm
d_A	Creepage distance in air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

Dimensions in mm (1 mm = 0.0394")



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = yellow, cathode = red

Type ZY 180L (L = Left for pin pair 4/5) } UL 758, style 1385,
Type ZY 180R (R = right for pin pair 6/7) } CSA class 5851, guide 460-1-1

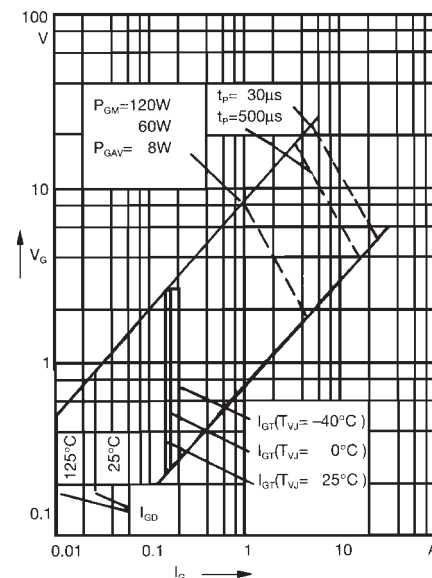


Fig. 1 Gate trigger characteristics

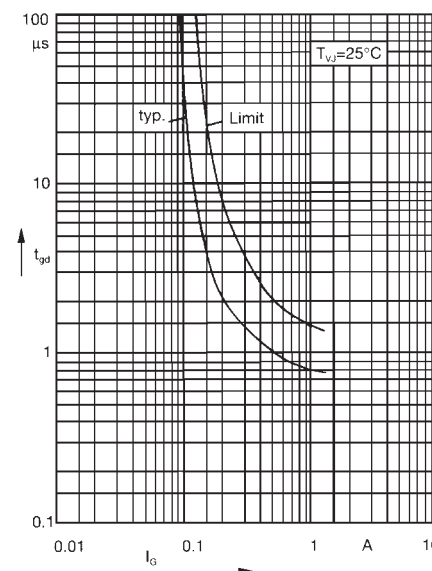


Fig. 2 Gate trigger delay time

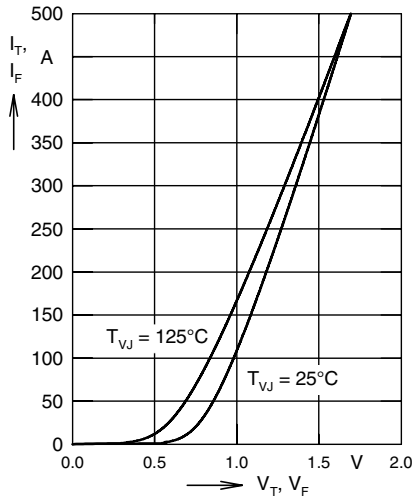


Fig 3: Forward current vs. voltage drop per thyristor/diode

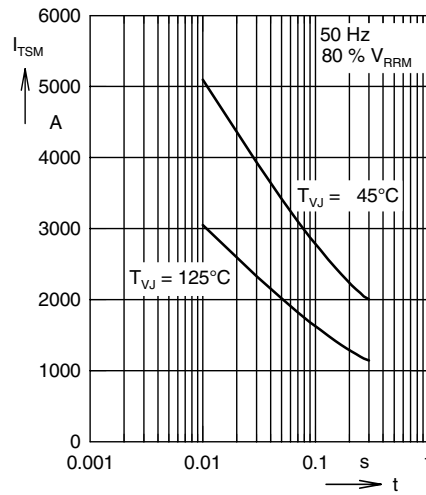


Fig 4: Surge overload current
 $I_{TSM}, I_{FSM} = f(t)$

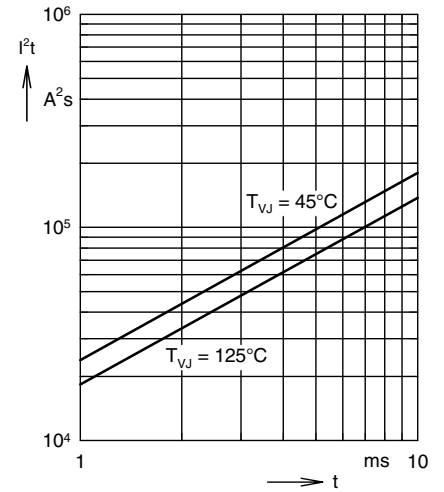


Fig 5: I^2t versus time per diode

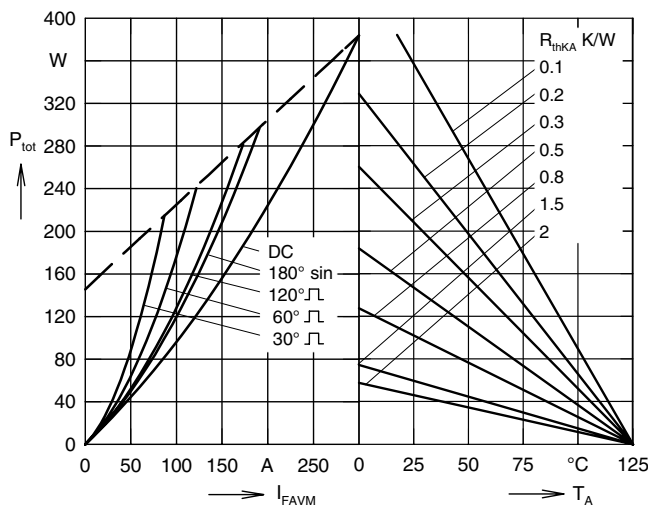


Fig 6: Power dissipation vs. on-state current and ambient temperature (per thyristor/diode)

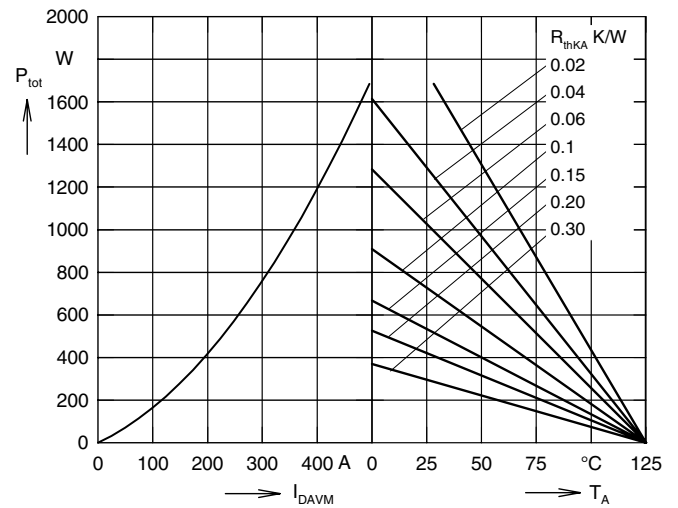


Fig 7: Power dissipation vs. direct output current and ambient temperature (three phase rectifier bridge)

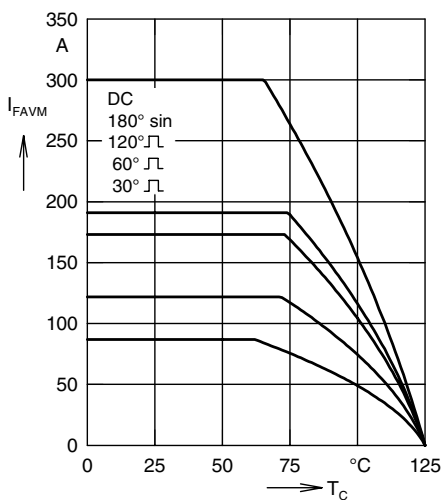


Fig 8: Maximum forward current at case temperature $I_{TAVM}, I_{DAVM} = f(T_C, d)$

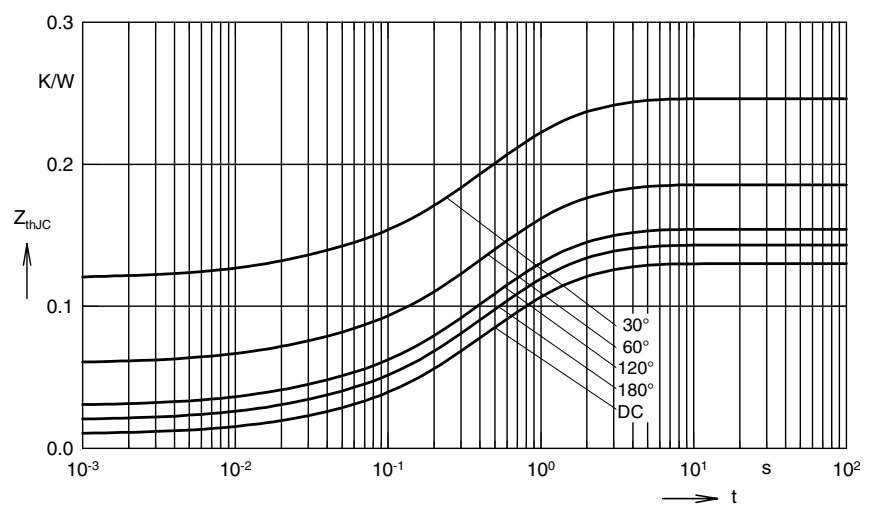


Fig 9: Transient thermal impedance junction to case Z_{thjC} at various conduction angles